

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	3	(US-20020046880-\$ or US-20010010627-\$).did. or (US-6995455-\$).did.	US-PGPUB; USPAT	OR	ON	2006/03/16 12:01
L5	3	L4 and conduct\$3	US-PGPUB; USPAT	OR	ON	2006/03/16 12:01
L6	3	L5 and electrode	US-PGPUB; USPAT	OR	ON	2006/03/16 12:01
L7	6	(US-20050208705-\$ or US-20050042786-\$ or US-20030113979-\$ or US-20020046880-\$ or US-20010010627-\$).did. or (US-6995455-\$).did.	US-PGPUB; USPAT	OR	ON	2006/03/16 12:07
L8	6	L7 and electrode and substrate	US-PGPUB; USPAT	OR	ON	2006/03/16 12:07
L9	17	(US-20050161753-\$ or US-20050042786-\$ or US-20050003606-\$ or US-20040241908-\$ or US-20040135168-\$ or US-20040132231-\$ or US-20030219969-\$ or US-20030122206-\$ or US-20030113979-\$ or US-20030017647-\$ or US-20020146859-\$ or US-20020048916-\$ or US-20010008794-\$).did. or (US-6964887-\$ or US-6911392-\$ or US-6815739-\$ or US-6429096-\$). did.	US-PGPUB; USPAT	OR	ON	2006/03/16 12:08

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L10	35	(US-20050253247-\$ or US-20050208705-\$ or US-20050042786-\$ or US-20050013544-\$ or US-20040201085-\$ or US-20040084206-\$ or US-20040056344-\$ or US-20040036164-\$ or US-20030219969-\$ or US-20030127747-\$ or US-20030052409-\$ or US-20030019568-\$ or US-20030017647-\$ or US-20030011070-\$ or US-20020146859-\$ or US-20020137330-\$ or US-20020053730-\$ or US-20020046880-\$ or US-20010028114-\$ or US-20010028104-\$ or US-20010020742-\$ or US-20010012643-\$ or US-20010010627-\$ or US-20010008794-\$ or US-20010003049-\$).did. or (US-6995455-\$ or US-6943442-\$ or US-6803324-\$ or US-6740981-\$ or US-6740964-\$ or US-6706546-\$ or US-6429096-\$ or US-6413798-\$ or US-6329610-\$ or US-5521435-\$). did.	US-PGPUB; USPAT	OR	ON	2006/03/16 12:08
L11	46	L10 or L9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 12:09
L12	29	l11 and (hole or via) near4 conduct\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:32
L13	1528	flip near2 chip and stack\$3 and conduct\$4 same layer and electrode and (hole or via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:42

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L14	551	I13 and semiconductor same (chip or device) and substrate and ((through near hole) or throughhole or through-hole)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 13:12
L15	81	I14 and electrode same conductor same insulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 13:19
L16	15	I15 and ((electrode same stack) or ((conductor same insulat\$4) same stack))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 13:14
L17	1	(US-6370013-\$).did.	USPAT	OR	ON	2006/03/16 14:32
L18	1	I17 and (hole or via) near4 conduct\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:33
L19	1	I18 and conduct\$4 near3 layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:34
L20	1	I18 and conduct\$4 near3 layer and insulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:34
L21	1	I18 and conduct\$4 near3 layer and insulat\$4 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:36
L22	1	I18 and conduct\$4 near3 layer and insulat\$4 and electrode and ((through near hole) or throughhole or through-hole)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:38

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L23	1	l17 and electrode and ((through near hole) or throughhole or through-hole)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:38
L24	160	flip near2 chip and stack\$3 and conduct\$4 same layer and electrode and (hole or via) and semiconductor same (chip or device) and substrate and (((through near hole) or throughhole or through-hole) same electrode) and (hole or via) near5 conduct\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 19:01
L25	182514	"438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 21:14
L26	1912	l25 and electrode same layer same ((through near hole) or throughhole or through-hole)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 16:25
L27	581	l26 and conduct\$3 same etch\$4 same (((through near hole) or throughhole or through-hole) same electrode or hole or via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 18:56
L28	16	(US-20050186801-\$ or US-20050148155-\$ or US-20050070099-\$ or US-20050035396-\$ or US-20050012109-\$ or US-20040147127-\$ or US-20020025587-\$ or US-20010024854-\$).did. or (US-6964887-\$ or US-6962865-\$ or US-6943056-\$ or US-6429096-\$ or US-6168992-\$ or US-6160284-\$ or US-6090699-\$ or US-5970339-\$). did.	US-PGPUB; USPAT	OR	ON	2006/03/16 17:57
L29	4	(US-20020025587-\$).did. or (US-6964887-\$ or US-6962865-\$ or US-6943056-\$).did.	US-PGPUB; USPAT	OR	ON	2006/03/16 18:55

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L30	4	I29 and conduct\$3 same etch\$4 same (((through near hole) or throughhole or through-hole) same electrode or hole or via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 18:56
L31	0	I20 and flip near2 chip and stack\$3 and conduct\$4 same layer and electrode and (hole or via) and semiconductor same (chip or device) and substrate and (((through near hole) or throughhole or through-hole) same electrode) and (hole or via) near5 conduct\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 19:02
L32	0	I20 and stack\$3 and conduct\$4 same layer and electrode and (hole or via) and substrate and (((through near hole) or throughhole or through-hole) same electrode) and (hole or via) near5 conduct\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 19:02
L33	0	I20 and conduct\$4 same layer and electrode and (hole or via) and substrate and (((through near hole) or throughhole or through-hole) same electrode) and (hole or via) near5 conduct\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 19:03
L34	1	I30 and flip near2 chip and stack\$3 and conduct\$4 same layer and electrode and (hole or via) and semiconductor same (chip or device) and substrate and (((through near hole) or throughhole or through-hole) same electrode) and (hole or via) near5 conduct\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 21:18
L35	4	I30 and conduct\$4 same layer and electrode and (hole or via) and substrate and (((through near hole) or throughhole or through-hole) same electrode) and (hole or via) near5 conduct\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 19:07
L36	4	I29 and conduct\$4 same layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 19:57

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L37	4	I36 and stack\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 19:57
L38	24812	438/15,104,107,108,109,110,111, 112,113,114,118,119,121,122,123, 125,126,127,128,129,135,142,145, 146,147,148,149,151,157,176,614, 615,637,667,406,455,456,457, 458,459,460,597,598,599,620.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 21:17
L39	29	I38 and flip near2 chip and stack\$3 and conduct\$4 same layer and electrode and (hole or via) and semiconductor same (chip or device) and substrate and (((through near hole) or throughhole or through-hole) same electrode) and (hole or via) near5 conduct\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 21:18
S14	182356	"438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 13:03
S15	363	S14 and flip near2 chip and stack\$3 and conduct\$4 same layer and electrode and (hole or via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 16:13
S16	79	S15 and stack same chip	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 13:24

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S17	17	(US-20050161753-\$ or US-20050042786-\$ or US-20050003606-\$ or US-20040241908-\$ or US-20040135168-\$ or US-20040132231-\$ or US-20030219969-\$ or US-20030122206-\$ or US-20030113979-\$ or US-20030017647-\$ or US-20020146859-\$ or US-20020048916-\$ or US-20010008794-\$).did. or (US-6964887-\$ or US-6911392-\$ or US-6815739-\$ or US-6429096-\$). did.	US-PGPUB; USPAT	OR	ON	2006/03/15 14:00
S18	1522	flip near2 chip and stack\$3 and conduct\$4 same layer and electrode and (hole or via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 16:24
S19	692	S18 and ((through near hole) or throughhole or through-hole)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 18:25
S20	546	S19 and semiconductor same (chip or device) and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 13:11
S22	130	masuda near kazuhiro	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 16:34

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S23	35	(US-20050253247-\$ or US-20050208705-\$ or US-20050042786-\$ or US-20050013544-\$ or US-20040201085-\$ or US-20040084206-\$ or US-20040056344-\$ or US-20040036164-\$ or US-20030219969-\$ or US-20030127747-\$ or US-20030052409-\$ or US-20030019568-\$ or US-20030017647-\$ or US-20030011070-\$ or US-20020146859-\$ or US-20020137330-\$ or US-20020053730-\$ or US-20020046880-\$ or US-20010028114-\$ or US-20010028104-\$ or US-20010020742-\$ or US-20010012643-\$ or US-20010010627-\$ or US-20010008794-\$ or US-20010003049-\$).did. or (US-6995455-\$ or US-6943442-\$ or US-6803324-\$ or US-6740981-\$ or US-6740964-\$ or US-6706546-\$ or US-6429096-\$ or US-6413798-\$ or US-6329610-\$ or US-5521435-\$). did.	US-PGPUB; USPAT	OR	ON	2006/03/15 17:39
S25	46	S23 or S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 17:45
S27	46	S23 or S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 18:24
S28	38	S27 and ((through near hole) or throughhole or through-hole)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 18:27

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S29	13	S27 and ((through near hole) or throughhole or through-hole) same electrode same layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 18:34
S30	6	(US-20030127747-\$ or US-20030052409-\$).did. or (US-6964887-\$ or US-6740964-\$ or US-6429096-\$ or US-5521435-\$). did.	US-PGPUB; USPAT	OR	ON	2006/03/15 18:33
S31	6	S30 and ((through near hole) or throughhole or through-hole) same electrode same layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 18:42
S32	3	S31 and conductor same ((through near hole) or throughhole or through-hole or via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 18:46
S33	22	S28 and conductor same ((through near hole) or throughhole or through-hole or via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 21:58
S34	22	S33 and flip near2 chip and stack\$3 and conduct\$4 same layer and electrode and (hole or via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 21:59
S35	6	(US-20050208705-\$ or US-20050042786-\$ or US-20030113979-\$ or US-20020046880-\$ or US-20010010627-\$).did. or (US-6995455-\$).did.	US-PGPUB; USPAT	OR	ON	2006/03/15 23:16
S36	6	S35 and electrode and substrate	US-PGPUB; USPAT	OR	ON	2006/03/15 23:18
S37	3	(US-20020046880-\$ or US-20010010627-\$).did. or (US-6995455-\$).did.	US-PGPUB; USPAT	OR	ON	2006/03/15 23:18
S38	3	S37 and electrode and substrate	US-PGPUB; USPAT	OR	ON	2006/03/15 23:55
S39	3	S38 and (insulat\$4 or dielectric)	US-PGPUB; USPAT	OR	ON	2006/03/15 23:36

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S40	3	S39 and etch\$4 same (hole or via or (through near hole) or throughhole or through-hole)	US-PGPUB; USPAT	OR	ON	2006/03/15 23:41
S41	3	S37 and conduct\$3	US-PGPUB; USPAT	OR	ON	2006/03/15 23:42
S42	3	S41 and electrode	US-PGPUB; USPAT	OR	ON	2006/03/15 23:56